

TENTATIVE

Features and Applications

- Low ON-state resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

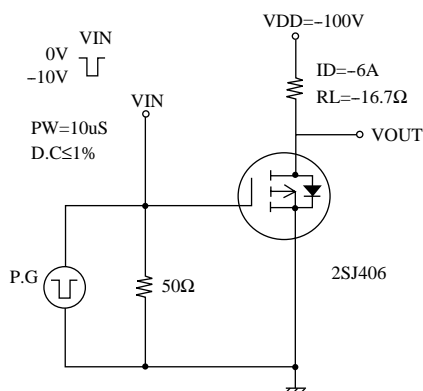
Absolute Maximum Ratings / Ta=25°C

			unit
Drain to Source Voltage	V _{DSS}	-200	V
Gate to Source Voltage	V _{GSS}	±20	V
Drain Current (D.C.)	I _D	-12	A
Drain Current (Pulse)	I _{DP}	PW≤10μS, dutycycle≤1%	-48 A
Allowable power Dissipation	P _D	Tc=25°C	40 W
Channel Temperature	T _{ch}		150 °C
Storage Temperature	T _{stg}		-55 to +150 °C

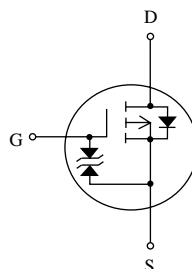
Electrical Characteristics / Ta=25°C

			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0	-200			V
Gate to Source Breakdown Voltage	V(BR)GSS	I _D =±100μA, V _{GS} =0	±20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-200V, V _{GS} =0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(OFF)}	V _{DS} =-10V, I _D =-1mA	-1.5		-2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-6A	6.3	10.5		S
Static Drain to Source on State Resistance	R _{DS(On)1}	I _D =-5A, V _{GS} =-4V		170	230	mΩ
Input Capacitance	C _{iss}	V _{DS} =-20V, f=1MHz		2400		pF
Output Capacitance	C _{oss}	V _{DS} =-20V, f=1MHz		540		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-20V, f=1MHz		260		pF
Turn-ON Delay Time	t _{d(On)}	See Specified Test Circuit .		40		ns
Rise Time	t _r		120		ns	
Turn-oFF Delay Time	t _{d(Off)}		720		ns	
Fall Time	t _f		310		ns	
Diode Forward Voltage	V _{SD}	I _S =-1.0A, V _{GS} =0	-1.0		-1.5	V

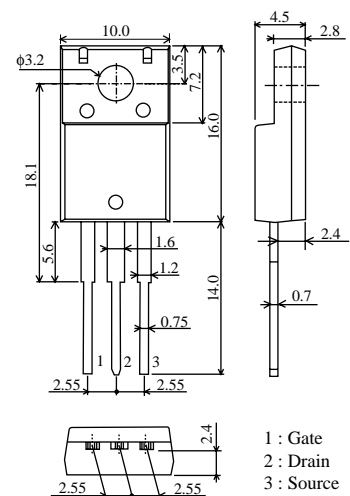
Switching Time Test Circuit



Electrical Connection



Case Outline TO-220 (unit:mm)



Specifications and information herein are subject to change without notice.

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